

AZ
Cmt

of [hard] an electrode material selected from a group consisting of nickel[, Ni] and copper.

21. (Amended) A mounting structure according to [any one of claims 8 to 19] claim 10, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of [soft] an electrode material selected from a group consisting of nickel and copper[, Cu].

Please add new claims 23-33:

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23. A semiconductor device according to claim 4, wherein a base material of said pyramidal bump electrodes is made of an electrode material selected from a group consisting of nickel and copper.

24. A semiconductor device according to claim 5, wherein a base material of said pyramidal bump electrodes is made of an electrode material selected from a group consisting of nickel and copper.

25. A mounting structure according to claim 11, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

26. A mounting structure according to claim 12, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from a group consisting of nickel and copper.

27. A mounting structure according to claim 13, wherein a base material of said pyramidal bump electrodes in said

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semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

28. A mounting structure according to claim 14, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

29. A mounting structure according to claim 15, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

30. A mounting structure according to claim 16, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

31. A mounting structure according to claim 17, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

32. A mounting structure according to claim 18, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.

33. A mounting structure according to claim 19, wherein a base material of said pyramidal bump electrodes in said semiconductor device is made of an electrode material selected from the group consisting of nickel and copper.